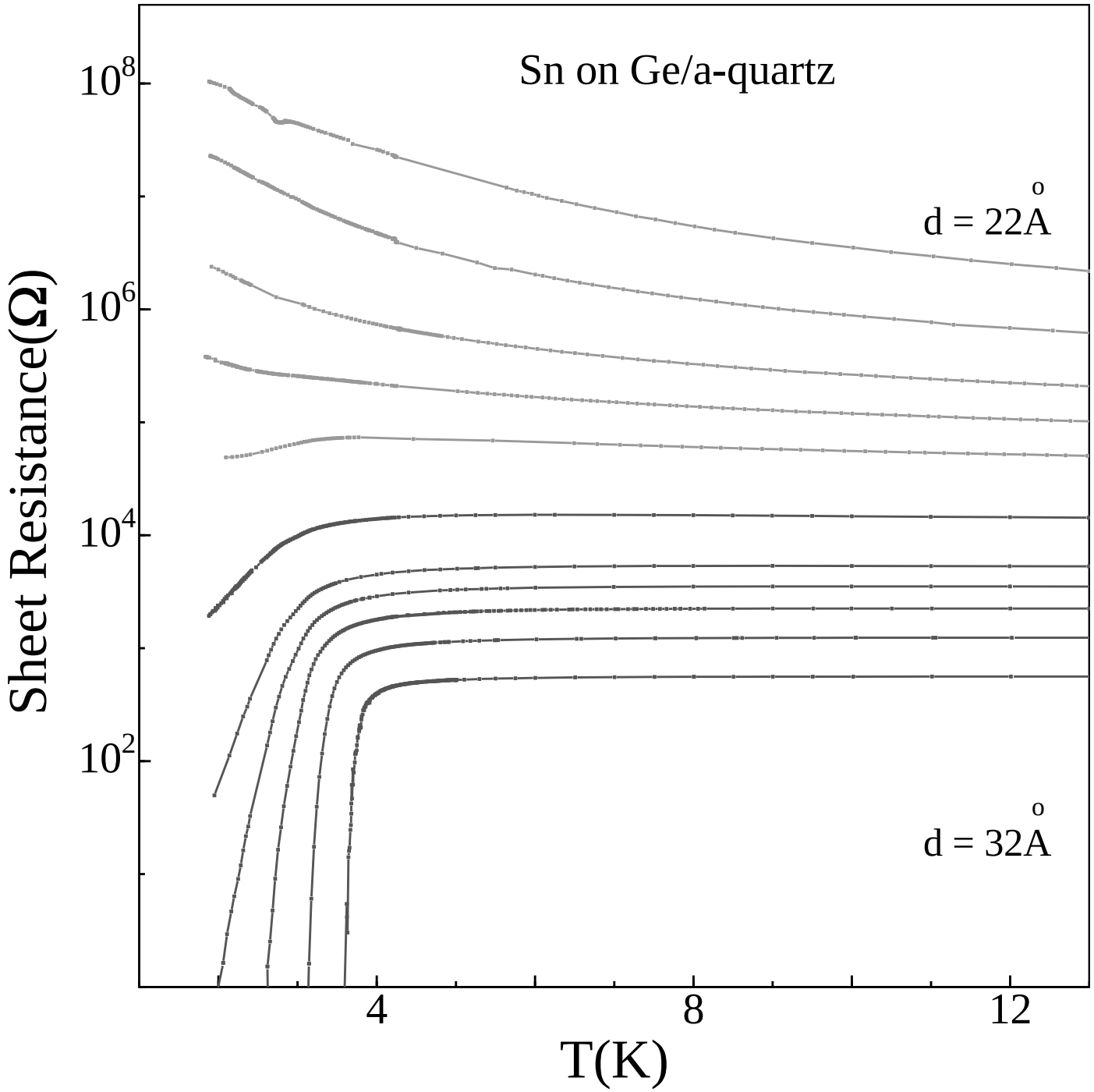
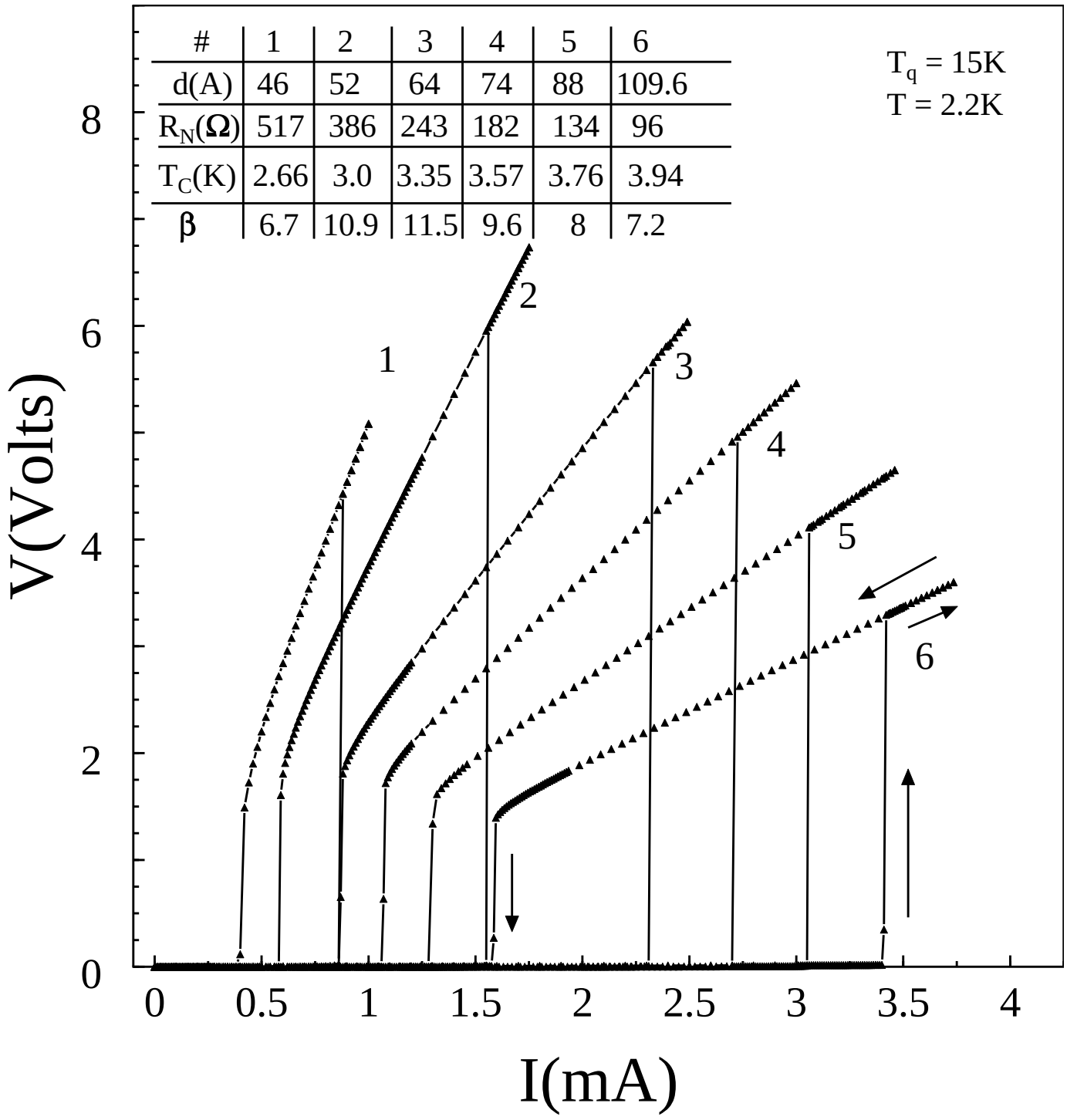
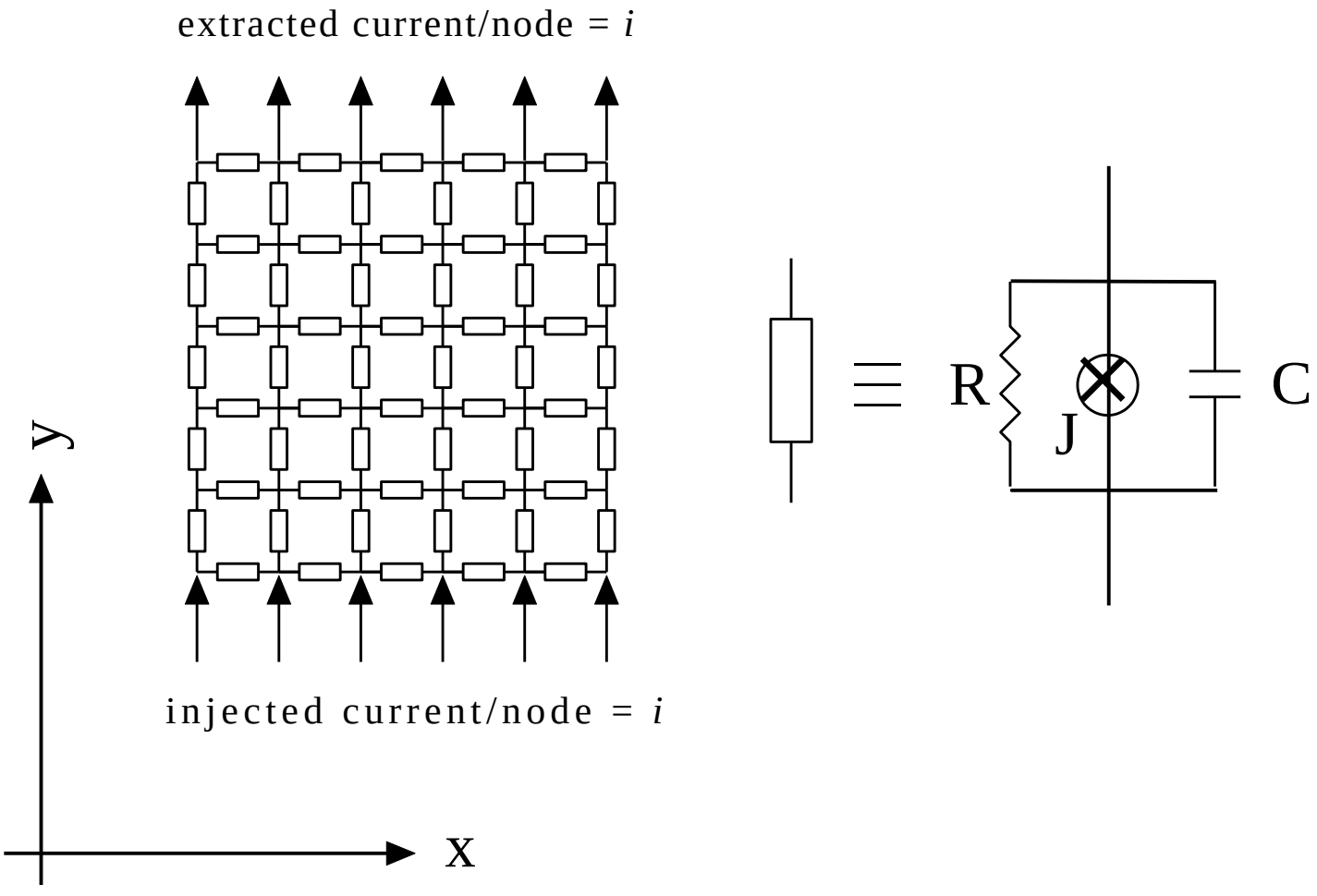
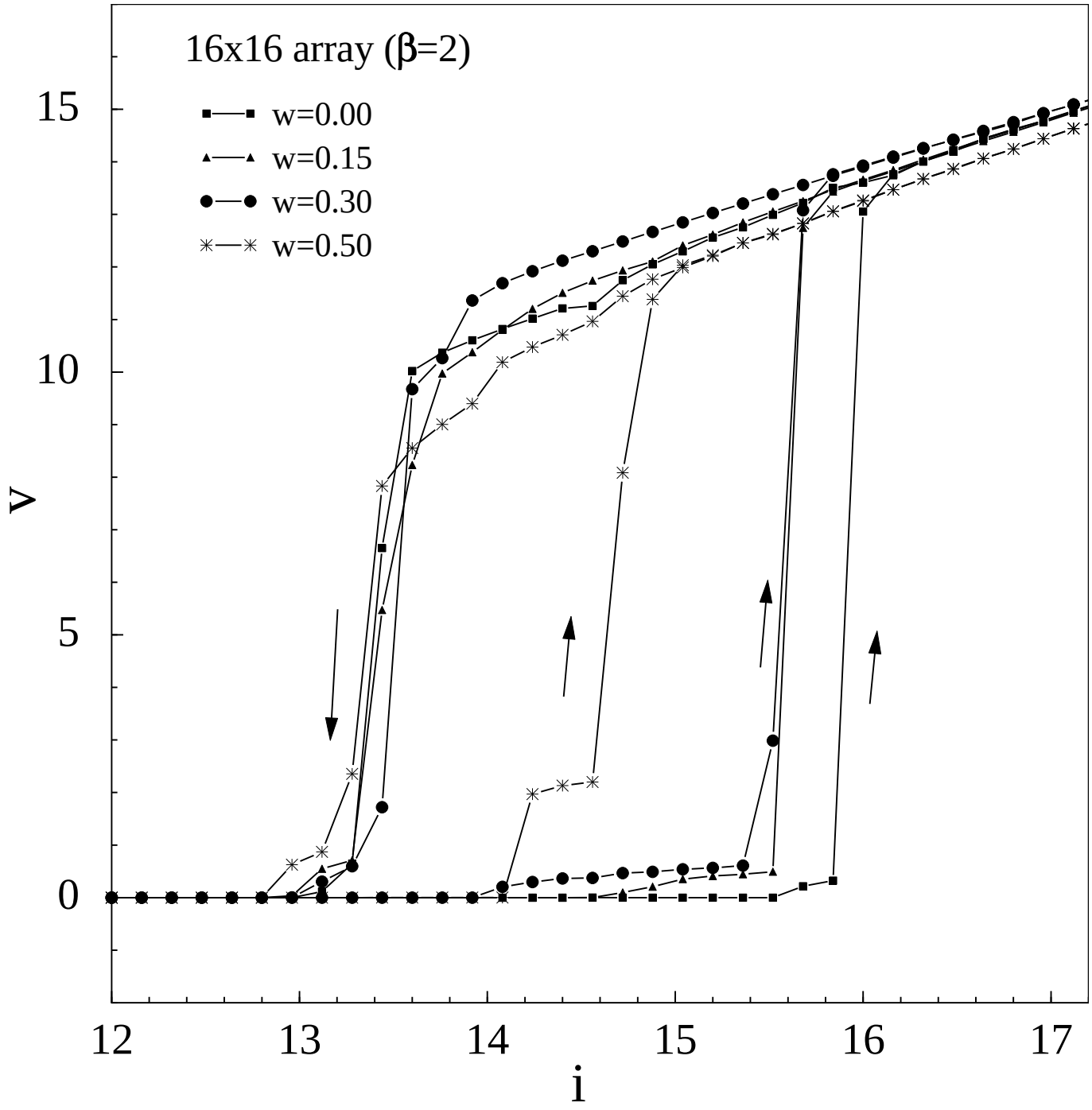
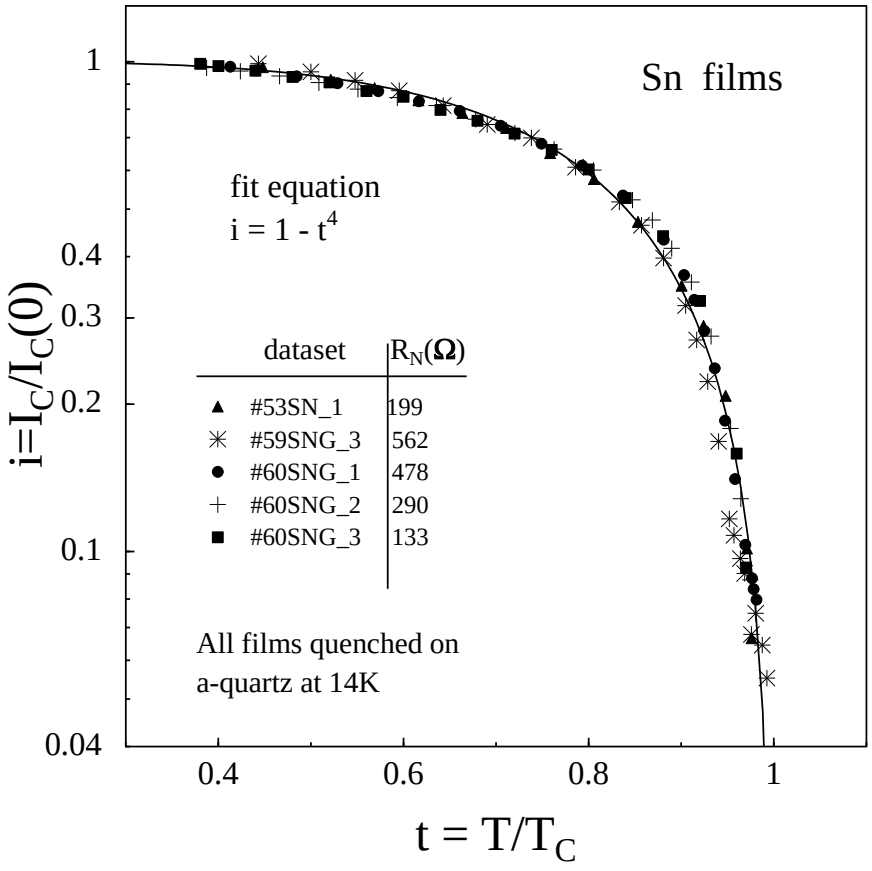

Sn on Ge/a-quartz
d = 22A
o
d = 32A
o
Sheet Resistance(Ω)
10^8
10^6
10^4
10^2
4
8
12
T(K)

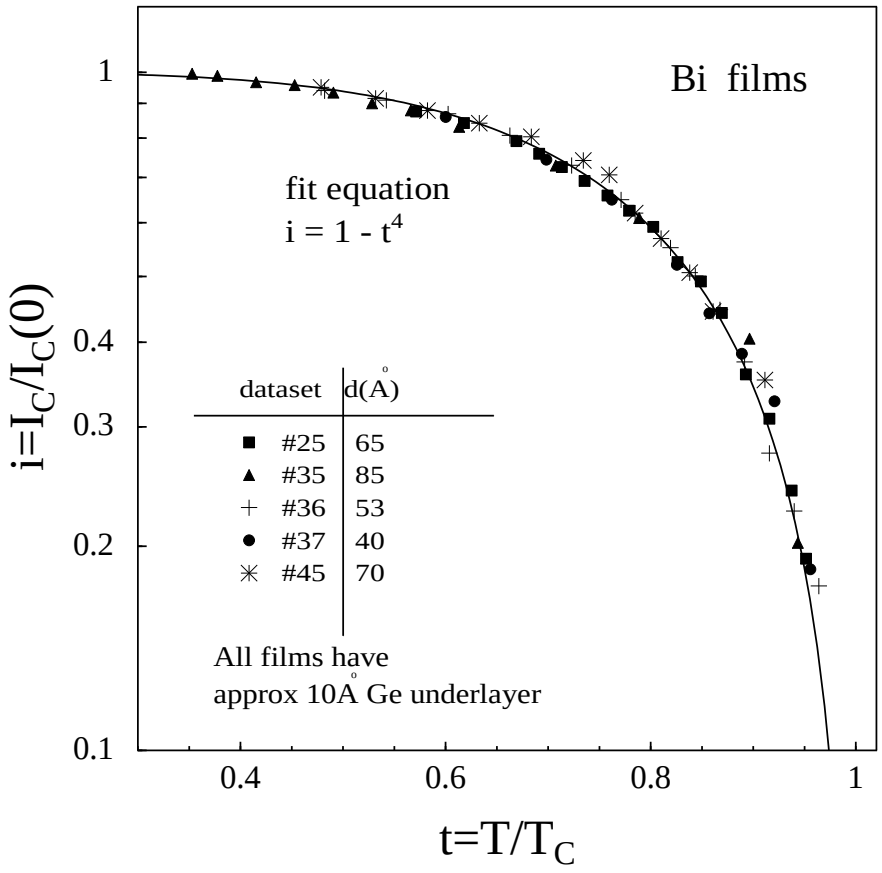


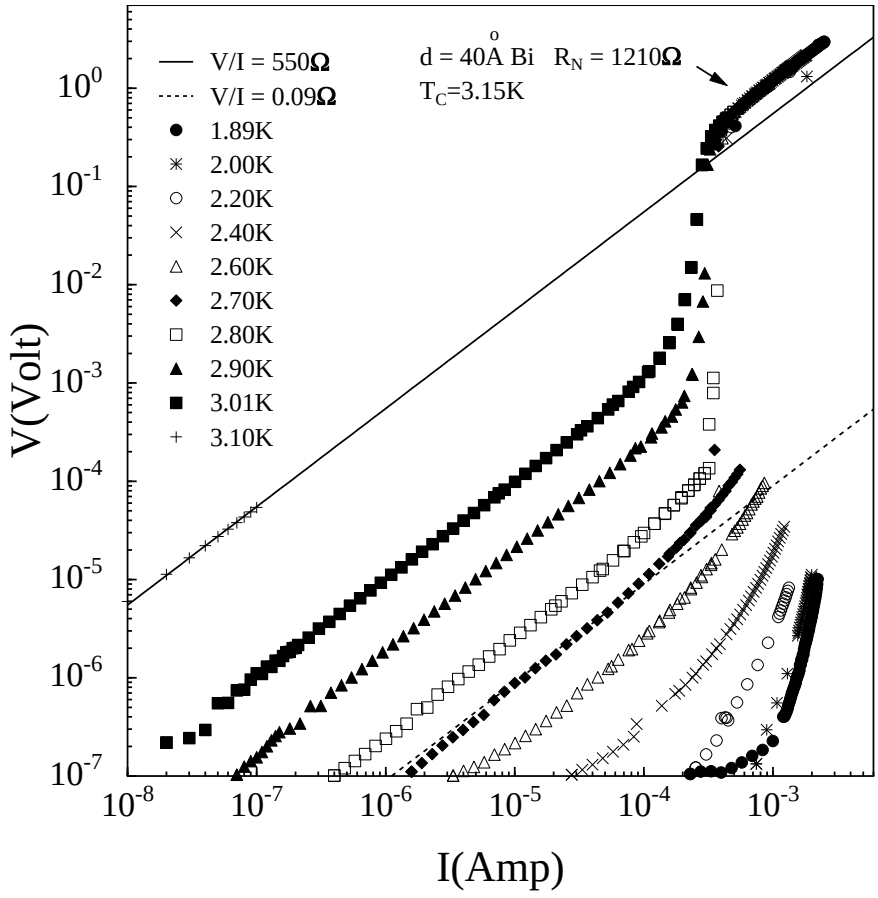
#	1	2	3	4	5	6
d(A)	46	52	64	74	88	109.6
$R_N(\Omega)$	517	386	243	182	134	96
T_C(K)	2.66	3.0	3.35	3.57	3.76	3.94
β	6.7	10.9	11.5	9.6	8	7.2

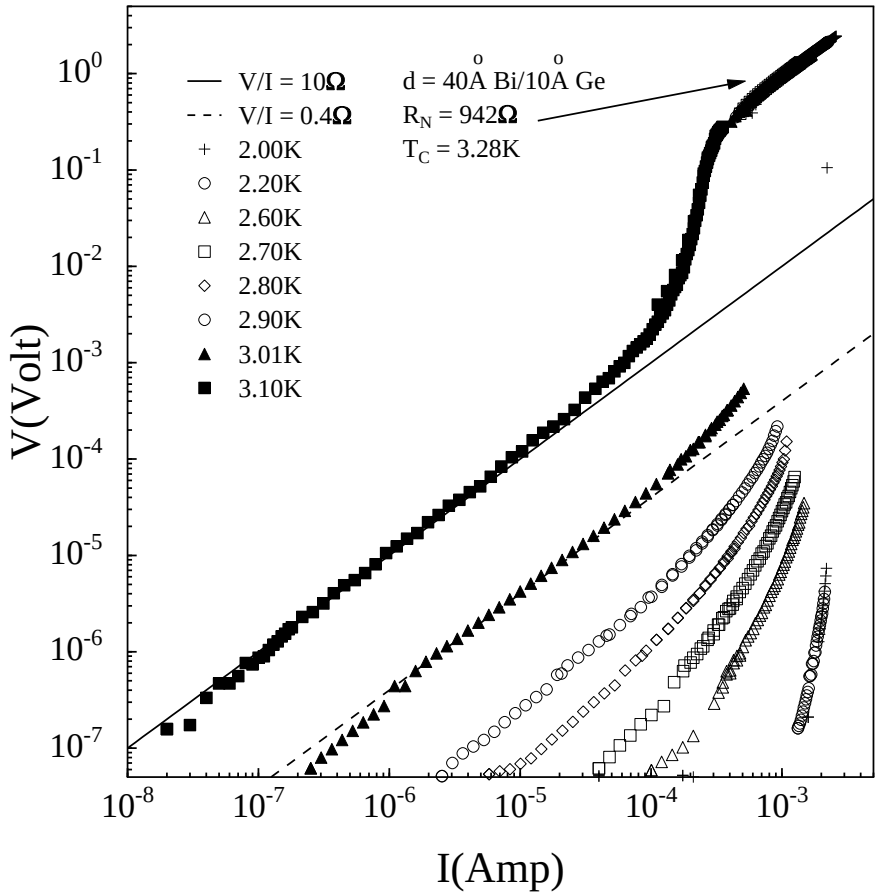

extracted current/node = i
injected current/node = i
y
X
R
J
C

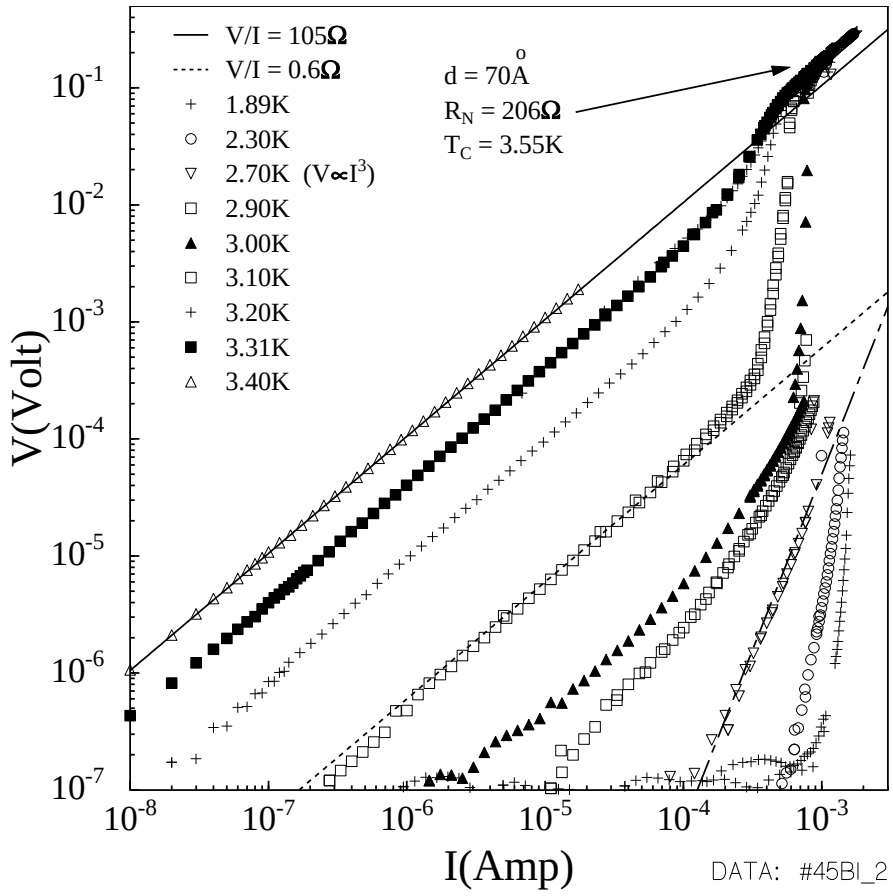

16x16 array (β=2)
w=0.00
w=0.15
w=0.30
w=0.50
15
10
5
0
v
12
13
14
15
16
17
i

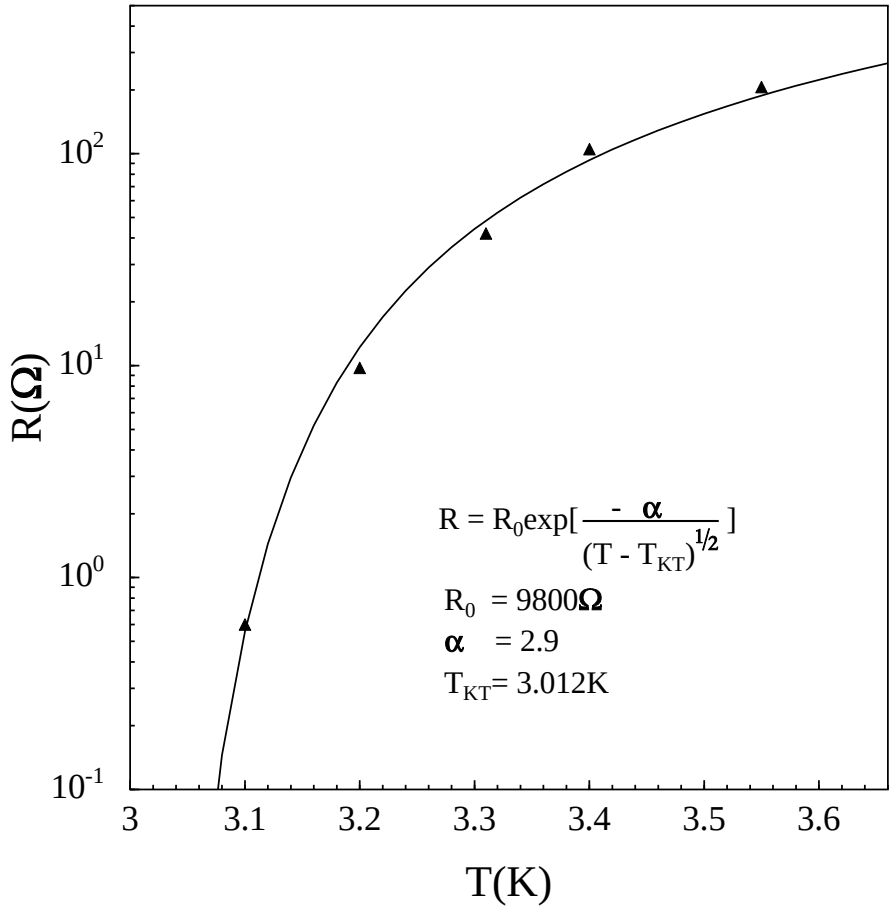

Sn films
fit equation
i = 1 - t^4
dataset | R_N(Ω)
#53SN_1 | 199
#59SNG_3 | 562
#60SNG_1 | 478
#60SNG_2 | 290
#60SNG_3 | 133
All films quenched on
a-quartz at 14K
i=I_C/I_C(0)
t = T/T_C
1
0.4
0.3
0.2
0.1
0.04
0.4
0.6
0.8
1

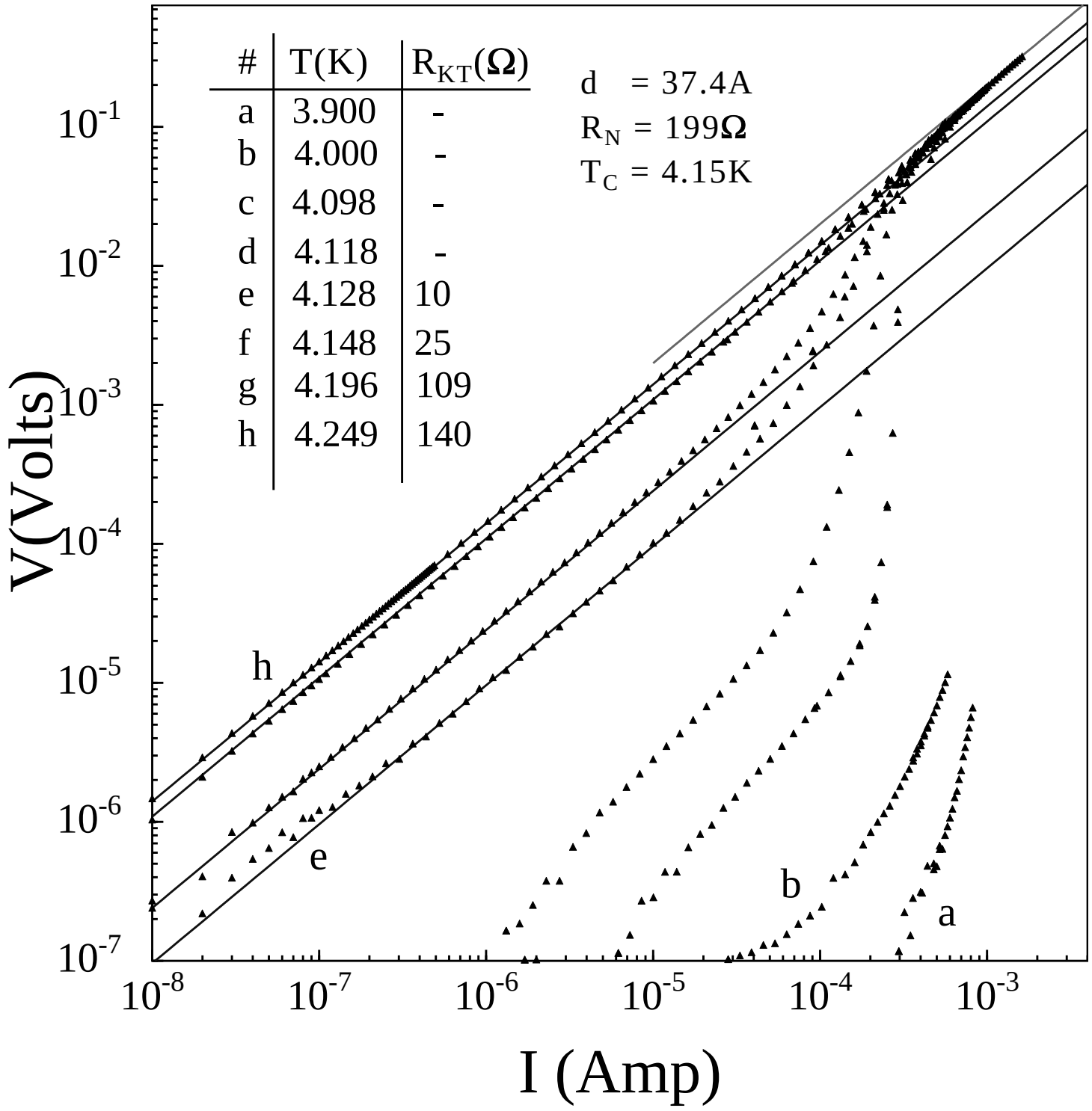

Bi films
fit equation
i = 1 - t^4
dataset | d(Å)
#25 | 65
#35 | 85
#36 | 53
#37 | 40
#45 | 70
All films have
approx 10Å Ge underlayer
i=I_C/I_C(0)
t=T/T_C
1
0.4
0.3
0.2
0.1
0.4
0.6
0.8
1


V/I = 550Ω
V/I = 0.09Ω
1.89K
2.00K
2.20K
2.40K
2.60K
2.70K
2.80K
2.90K
3.01K
3.10K
d = 40Å Bi R_N = 1210Ω
T_C=3.15K
V(Volt)
I(Amp)


V/I = 10Ω
V/I = 0.4Ω
2.00K
2.20K
2.60K
2.70K
2.80K
2.90K
3.01K
3.10K
d = 40Å Bi/10Å Ge
R_N = 942Ω
T_C = 3.28K
V(Volt)
I(Amp)


V/I = 105Ω
V/I = 0.6Ω
1.89K
2.30K
2.70K (V∝I³)
2.90K
3.00K
3.10K
3.20K
3.31K
3.40K
d = 70Å
R_N = 206Ω
T_C = 3.55K
V(Volt)
I(Amp)
DATA: #45BI_2


R = R₀exp[- α / (T - T_KT)^½]
R₀ = 9800Ω
α = 2.9
T_KT = 3.012K
R(Ω)
T(K)


#
T(K)
R_KT(Ω)
a 3.900 -
b 4.000 -
c 4.098 -
d 4.118 -
e 4.128 10
f 4.148 25
g 4.196 109
h 4.249 140
d = 37.4A
R_N = 199Ω
T_C = 4.15K
V(Volts)
I (Amp)
10^-1
10^-2
10^-3
10^-4
10^-5
10^-6
10^-7
10^-8
10^-7
10^-6
10^-5
10^-4
10^-3
h
e
b
a